CLAIMS

46 ~~33~~. (Amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer proximate the polycrystalline thin film transistor layer, the fluorine-containing layer comprising tungsten; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine-containing layer.

47 ~~34~~. The method of claim 33 wherein the polycrystalline thin film transistor layer comprises silicon.

48 ~~35~~. (Amended) The method of claim 33 wherein the forming a fluorine-containing layer comprises chemical vapor deposition utilizing WF_6 and SiH_4 precursors.

49 ~~36~~. (Amended) The method of claim 35 further comprising, after the transferring fluorine, removing the fluorine-containing layer from over the thin film transistor layer.

Appl. No. 09/902,277

50 ~~37~~. (Amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer over the transistor gate and over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine-containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer over the transistor gate from the fluorine-containing layer.

51 ~~38~~. (New) The method of claim 37 wherein the fluorine-containing layer comprises tungsten.

52 ~~39~~. (New) The method of claim 37 wherein the buffering layer comprises SiO_2.

53 ~~40~~. (New) The method of claim 37 wherein the polycrystalline thin film transistor layer comprises germanium.

E1 end

Rule 1.126 E2